Peng Dong

List of Publications by Year
in descending order

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25	224	1163117 8	996975 15
papers	citations	h-index	g-index

25	25	25	150
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Impurity engineering of Czochralski silicon. Materials Science and Engineering Reports, 2013, 74, 1-33.	31.8	52
2	Germanium effect on oxygen precipitation in Czochralski silicon. Journal of Applied Physics, 2004, 96, 4161-4165.	2.5	33
3	Germanium-doped Czochralski silicon for photovoltaic applications. Solar Energy Materials and Solar Cells, 2011, 95, 2466-2470.	6.2	24
4	Light-induced beneficial ion accumulation for high-performance quasi-2D perovskite solar cells. Energy and Environmental Science, 2022, 15, 2499-2507.	30.8	18
5	Synergistic effects of bithiophene ammonium salt for high-performance perovskite solar cells. Journal of Materials Chemistry A, 2022, 10, 9971-9980.	10.3	14
6	Effect of germanium on the kinetics of boron-oxygen defect generation and dissociation in Czochralski silicon. Applied Physics Letters, 2010, 97, 162107.	3.3	12
7	Electron Radiation Effects on the 4H-SiC PiN Diodes Characteristics: An Insight From Point Defects to Electrical Degradation. IEEE Access, 2019, 7, 170385-170391.	4.2	8
8	Understanding the Influence of Cation and Anion Migration on Mixedâ€Composition Perovskite Solar Cells via Transient Ion Drift. Physica Status Solidi - Rapid Research Letters, 2021, 15, 2100225.	2.4	8
9	Sample thickness effect of thermal vibration correction within X-ray dynamical theory for germanium-doped silicon. Journal of Applied Physics, 2017, 121, 125704.	2.5	7
10	Atomistic Mechanism of 4 H - <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline" overflow="scroll"><mml:mrow><mml:mi>Si</mml:mi><mml:mi mathvariant="normal">C</mml:mi></mml:mrow><mml:mo>/</mml:mo><mml:msub><mml:mrow><mml:mi>Si</mml:mi><mml:mi mathvariant="normal">O</mml:mi></mml:mrow><mml:mn>2</mml:mn></mml:msub></mml:math> Interface Carrier-Trapping Effects on Breakdown-Voltage Degradation in Power Devices. Physical Review Applied, 2021, 15, .	3.8	7
11	Quantitative Study of the Evolution of Oxygen and Vacancy Complexes in Czochralski Silicon. Applied Physics Express, 2012, 5, 021302.	2.4	6
12	Study of gamma-ray radiation effects on the passivation properties of atomic layer deposited Al2O3 on silicon using deep-level transient spectroscopy. Journal of Materials Science: Materials in Electronics, 2019, 30, 1148-1152.	2.2	6
13	Relating Gain Degradation to Defects Production in Neutron-Irradiated 4H-SiC Transistors. IEEE Transactions on Nuclear Science, 2021, 68, 312-317.	2.0	6
14	Effects of Neutron Irradiation on the Static and Switching Characteristics of High-Voltage 4H-SiC p-type Gate Turn-off Thyristors. IEEE Transactions on Electron Devices, 2019, 66, 3910-3915.	3.0	5
15	Effect of germanium doping on the formation kinetics of vacancy-dioxygen complexes in high dose neutron irradiated crystalline silicon. Journal of Applied Physics, 2017, 122, 095704.	2.5	4
16	Optimized phosphorus diffusion process and performance improvement of c-Si solar cell by eliminating SiP precipitates in the emitter. Journal of Materials Science: Materials in Electronics, 2019, 30, 13820-13825.	2.2	3
17	Boron deactivation in heavily boron-doped Czochralski silicon during rapid thermal anneal: Atomic level understanding. Applied Physics Letters, 2014, 104, 032102.	3.3	2
18	Effect of Germanium Doping on the Production and Evolution of Divacancy Complexes in Neutron Irradiated Czochralski Silicon. Journal of Electronic Materials, 2018, 47, 5019-5024.	2.2	2

#	Article	IF	Citations
19	Electronic and doping properties of hexagonal silicon carbide with stacking faults induced cubic inclusions. Journal of Applied Physics, 2021, 129, .	2.5	2
20	Enhanced internal gettering in n/n+ epitaxial silicon wafer: coaction of nitrogen impurity and vacancy on oxygen precipitation in substrate. Journal of Materials Science: Materials in Electronics, 2014, 25, 3486-3491.	2.2	1
21	Carbon effect on the survival of vacancies in Czochralski silicon during rapid thermal anneal. Journal of Applied Physics, 2017, 122, 045705.	2.5	1
22	Studies of annealing of point defects and their influence on the electrical degradation and recovery behaviors of heavily neutron irradiated silicon. Radiation Effects and Defects in Solids, 2018, 173, 1018-1026.	1.2	1
23	Forward Voltage Drop Induced by an Abnormal Threading Dislocation Aggregation in 4H-SiC GTO Devices. Materials, 2019, 12, 4042.	2.9	1
24	Effect of Ultraviolet Irradiation on 4H-SiC PiN Diodes Characteristics. Nanoscale Research Letters, 2021, 16, 141.	5.7	1
25	Influence of ion implantation and high temperature Ar annealing on carrier lifetime in n-type 4H-SiC epilayers. , 2020, , .		0